

# Voltage Variable Absorptive Attenuator

## DC - 2 GHz

# AT-250

V 2.00

### Features

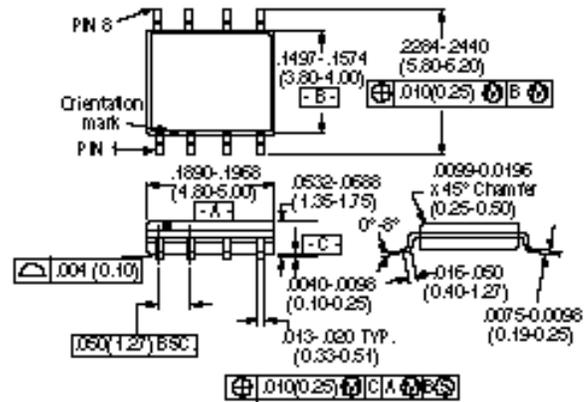
- 12 dB Voltage Variable Attenuation
- Low Intermodulation Products
- Low DC Power Consumption: 50  $\mu$ W
- Single Voltage Control 0 to -4 Volts
- Nanosecond Switching Speed
- Temperature Range: -40°C to +85°C
- Low Cost SOIC 8 Lead Plastic Package
- Tape and Reel Packaging Available<sup>1</sup>

### Description

M/A-COM's AT-250 is a GaAs MMIC voltage variable absorptive attenuator in a low cost SOIC 8-lead surface mount plastic package. The AT-250 is ideally suited for use where attenuation fine tuning, fast switching and very low power consumption are required. Typical applications include radio, cellular, GPS equipment and other Automatic Gain/Level Control circuits.

The AT-250 is fabricated with a monolithic GaAs MMIC using a mature 1-micron process. The process features full chip passivation for increased performance and reliability.

### SO-8



8-Lead SOP outline dimensions  
Narrow body .150  
(All dimensions per JEDEC No. MS-012-AA, Issue C)  
Dimensions in ( ) are in mm.  
Unless Otherwise Noted: xxx =  $\pm 0.10$  (xxx =  $\pm 0.25$ )  
xx =  $\pm 0.02$  (x =  $\pm 0.5$ )

### Ordering Information

Part Number	Package
AT-250 PIN	SOIC 8-Lead Plastic Package
AT-250TR	Forward Tape & Reel
AT-250RTR	Reverse Tape & Reel

### Electrical Specifications, $T_A = +25^\circ\text{C}$

Parameter	Test Conditions <sup>2</sup>	Unit	Min.	Typ.	Max.
Insertion Loss	DC - 0.1 GHz	dB		2.9	3.1
	DC - 0.5 GHz	dB		3.0	3.2
	DC - 1.0 GHz	dB		3.2	3.5
	DC - 2.0 GHz	dB		3.4	3.8
Flatness (Peak to Peak)	DC - 0.1 GHz	dB		+/- 0.1	+/- 0.3
	DC - 0.5 GHz	dB		+/- 0.2	+/- 0.4
	DC - 1.0 GHz	dB		+/- 0.5	+/- 0.8
	DC - 2.0 GHz	dB		+/- 1.2	+/- 1.5
VSWR				2.1:1	
Trise, Tfall Ton, Toff Transients	10% to 90% RF, 90% to 10% RF	nS		3	
	50% Control to 90% RF, 50% Control to 10% RF	nS		5	
	In Band	mV		10	
Power Handling	Linear Operation	dBm			13
	Absolute Max Input Power	dBm			21
IP <sub>2</sub>	Measured Relative to Input Power (For two-tone Input Power Up to +5 dBm)	dBm	28	34	
	0.05 GHz 0.5 - 2.0 GHz	dBm	40	47	
IP <sub>3</sub>	Measured Relative to Input Power (For two-tone Input Power Up to +5 dBm)	dBm	18	31 <sup>(3)</sup>	
	0.05 GHz 0.5 - 2.0 GHz	dBm	18.5	36 <sup>(3)</sup>	

1. Refer to "Tape and Reel Packaging" Section, or contact factory.

2. All measurements at 1 GHz in a 50  $\Omega$  system, unless otherwise specified. A control voltage 0 to -4 volts @ 20  $\mu$ A typ.

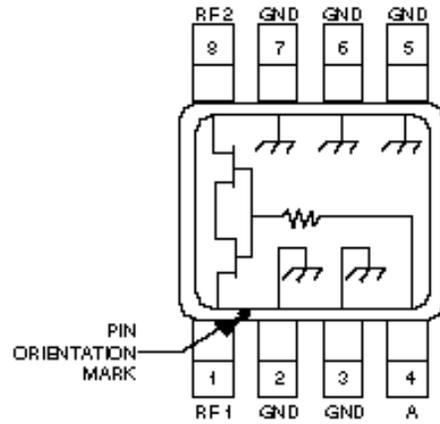
3. For levels above 6 dB attenuation. For levels below 6 dB, the minimum specification numbers apply.

## Absolute Maximum Ratings<sup>1</sup>

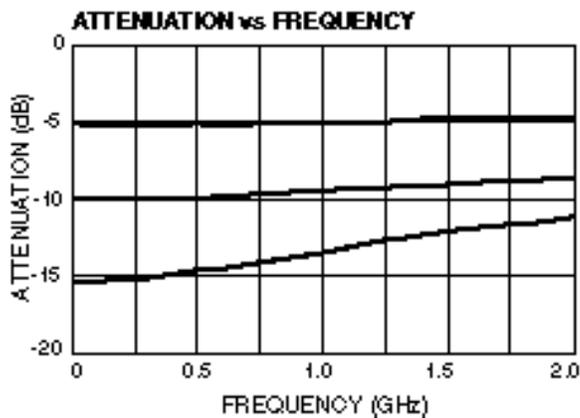
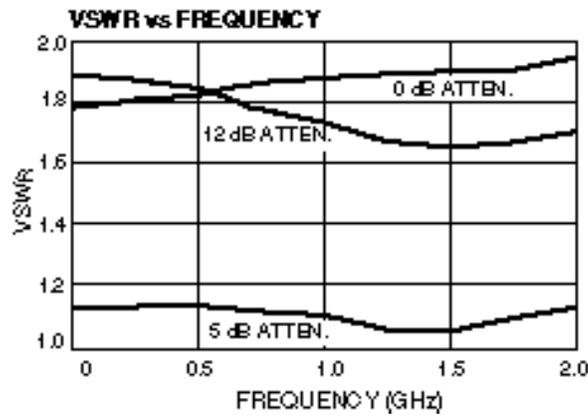
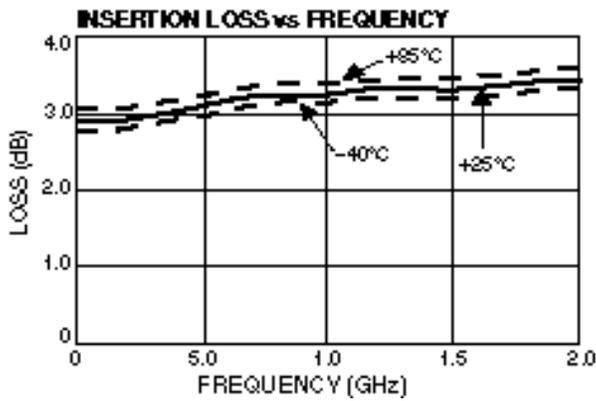
Parameter	Absolute Maximum
Max. Input Power	+21 dBm
Control Voltage	+5 V, -8.5 V
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

1.Operation of this device above any one of these parameters may cause permanent damage.

## Functional Schematic



## Typical Performance



## Pin Configuration

Pin No.	Description
1	RF1
2	GND
3	GND
4	A
5	GND
6	GND
7	GND
8	RF2

